

THGEM production by Print Electronics

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Print Electronics

- Company was presented in RD51 meeting at CERN held in November 2011
- Produced many THGEMs for WIS with rim etched by standard photo-lithography
- Expressed high interest in producing large area THGEMs

- Current production technique adapted from Rui
 - <http://indico.cern.ch/contributionDisplay.py?sessionId=5&contribId=39&confId=158402>
 - Rims are made with chemical etching

Goals

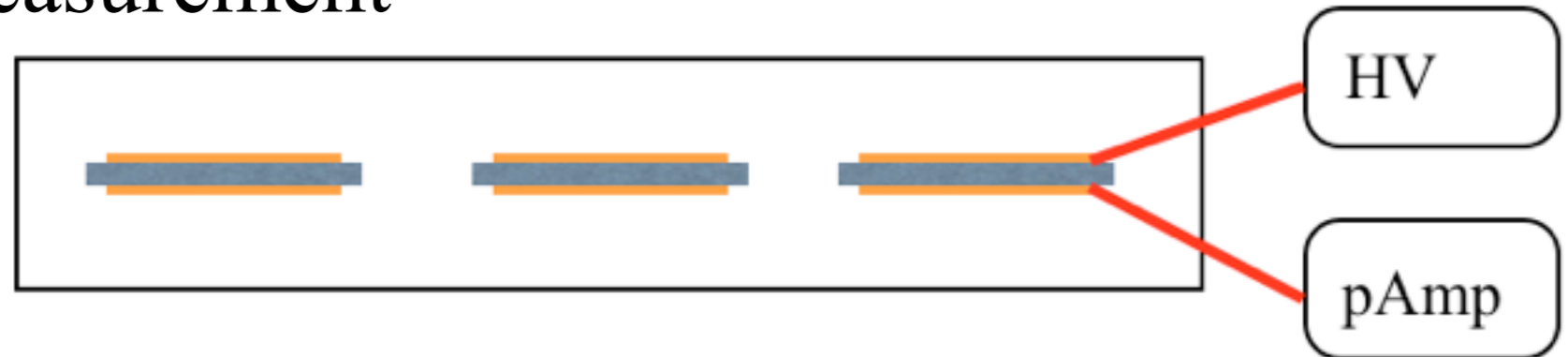
- Produce high-quality large-area THGEMs
- Rim sizes from 5 μm to 100 μm
- Large scales
 - Present needs: COMPASS RICH, DHCAL for ILC
 - We started with 30 \times 30 mm² electrodes
 - The first batch of 100 \times 100 mm² electrodes is evaluated these days
 - The next step is segmented 300 \times 300 mm² electrode

PE/WIS combined effort

- Production at PE according to WIS specs
- Quality control tests at WIS
- The following parameters are measured and compared
 - **Microscopy**: drilling and etching quality
 - **Dark current** under high voltage and controlled conditions
 - **Gain curve and maximal achievable gain**
 - measured in single THGEM structure using 8 KeV x-rays in pulse mode
 - Spark rate without source
 - work in progress
- WIS feedback improved production quality
- We plan a systematic comparison between PE production and Rui's

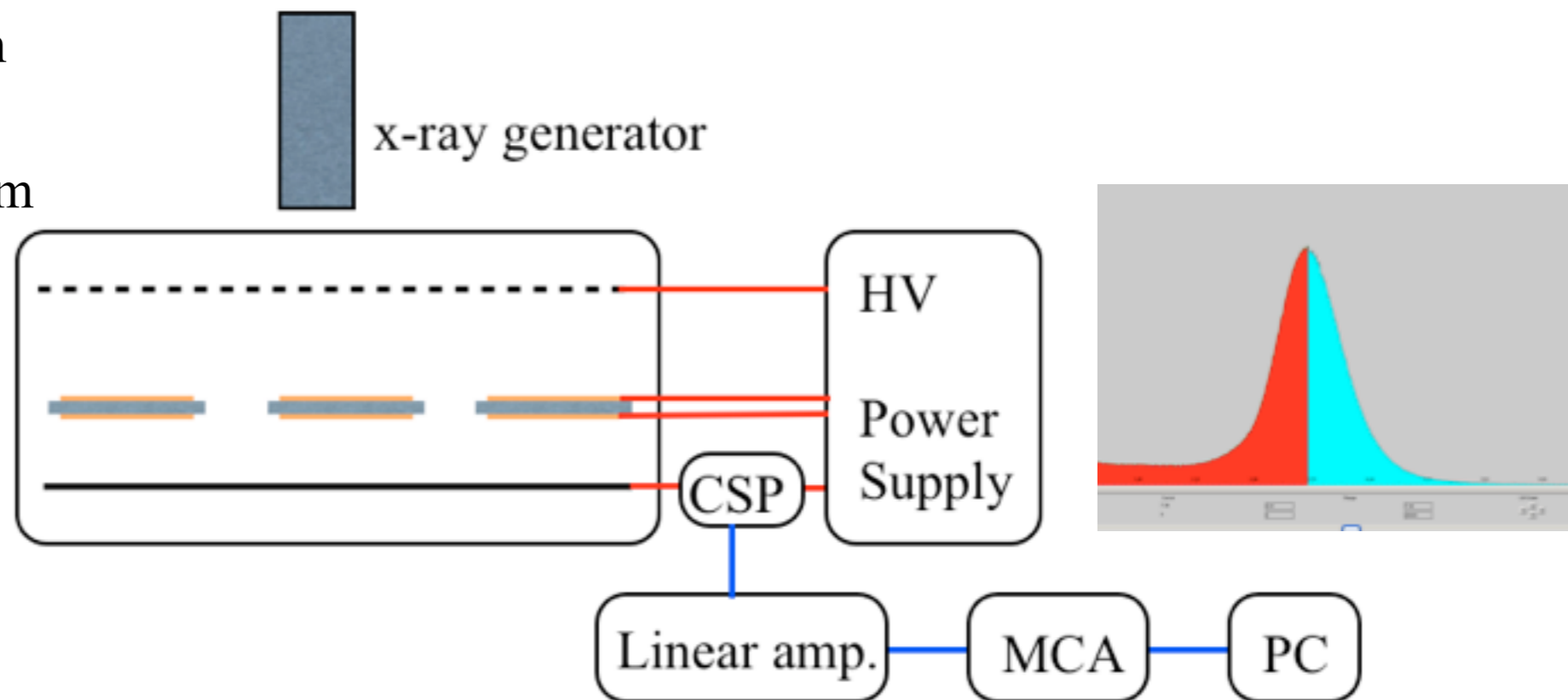
Test setups

- Dark current measurement



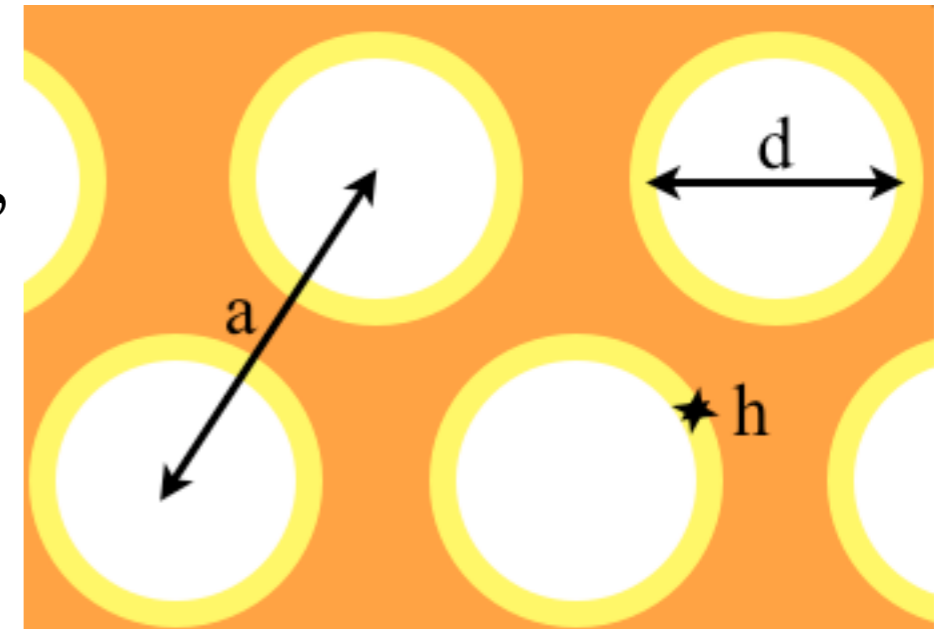
- Gain curve

- Gas NeCH₄(5%)
- Source: 8KeV photons
- Drift gap: 6.5 mm
- Drift fields: 0.5 kV/cm
- Induction gap: 2mm
- Induction field: 1kV/cm

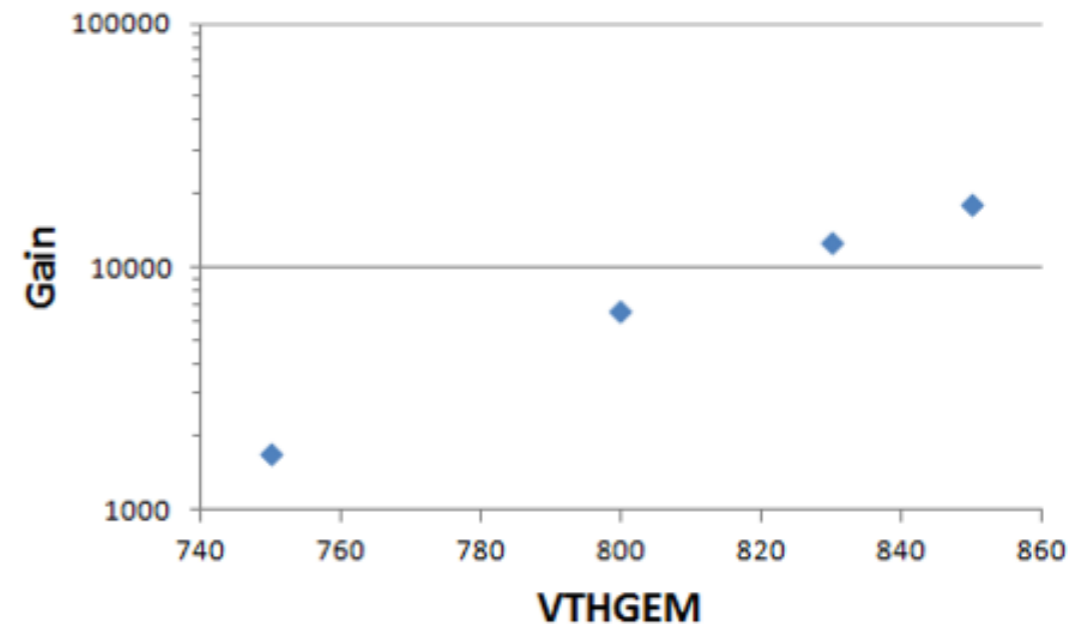


March 2012 batch - $30 \times 30 \text{ mm}^2$ electrodes

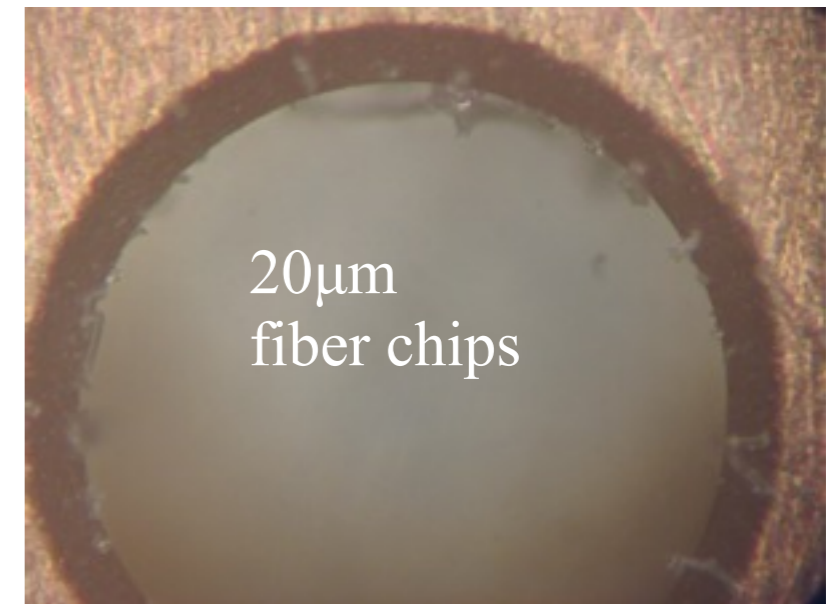
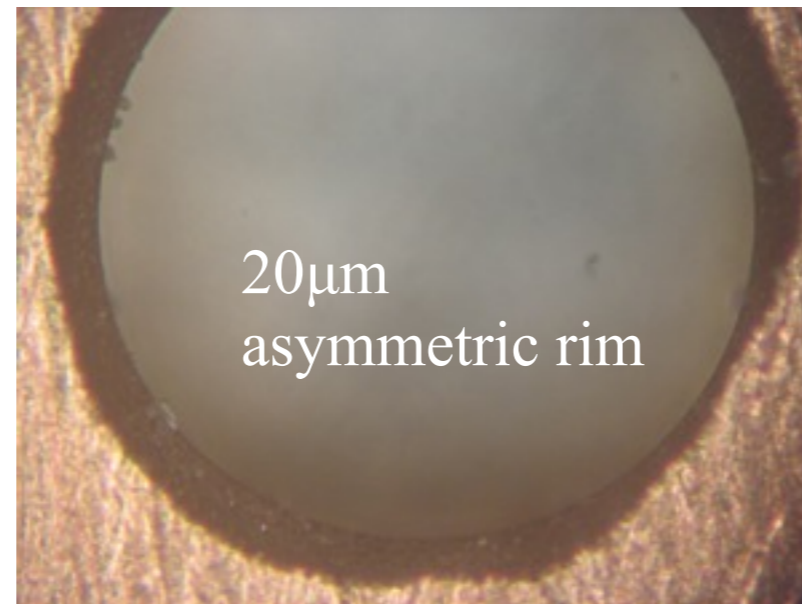
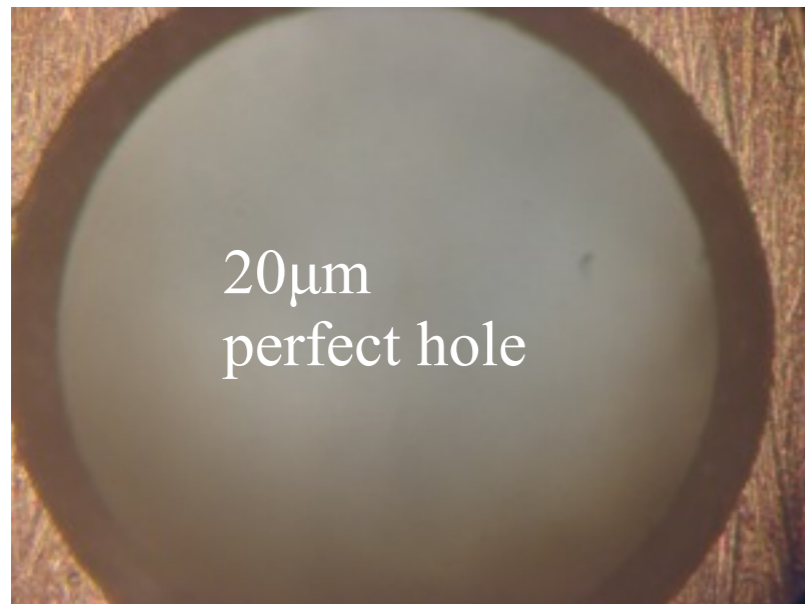
- Geometry:
- $a = 1 \text{ mm}$, $d = 0.5 \text{ mm}$, $t = 0.4 \text{ mm}$,
 $h = 100 / 50 / 20 \text{ }\mu\text{m}$
- Dark currents:
 - $h = 100 \text{ }\mu\text{m} \rightarrow 10 \text{ pA} - 2 \text{ nA @ } 1 \text{ kV}$
 - $h = 50 \text{ }\mu\text{m} \rightarrow < 1 \text{ nA @ } 1 \text{ kV}$
 - $h = 20 \text{ }\mu\text{m} \rightarrow < 1 \text{ nA @ } 1 \text{ kV}$
- Maximal achievable gain
@ $\text{NeCH}_4(5\%)$:
 - $h = 100 \text{ }\mu\text{m} \rightarrow 2 \times 10^4$
 - $h = 50 \text{ }\mu\text{m} \rightarrow 6 \times 10^3$
- Sparks occur quite often



100 μm rims



March 2012 batch - snapshots of defects

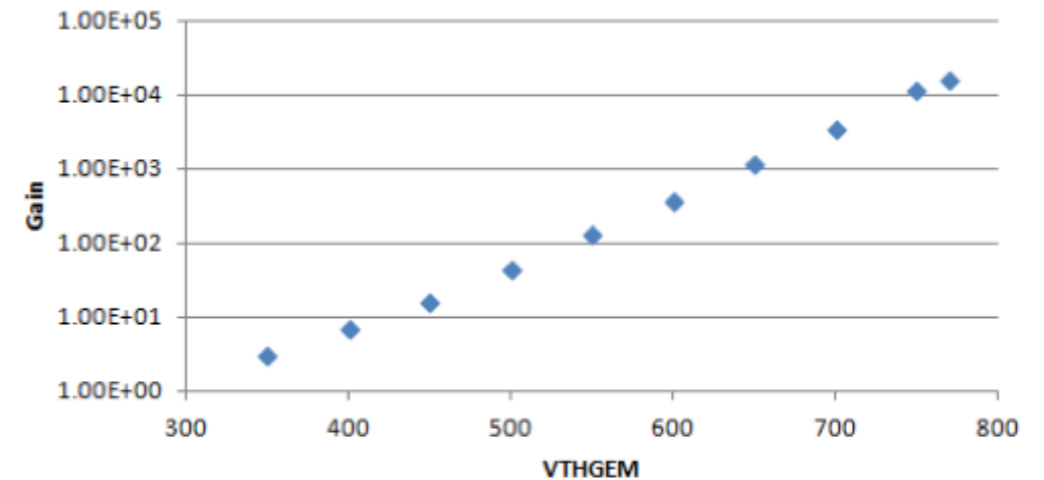


- We consulted with Rui who suggested the following
 - The asymmetric holes are due to remains of epoxy affecting the chemical etching → pointed at a problem in the de-smearing stage
 - The fiber chips can be removed with high pressure Nitrogen flush
- In addition, a problem in the baking step was found

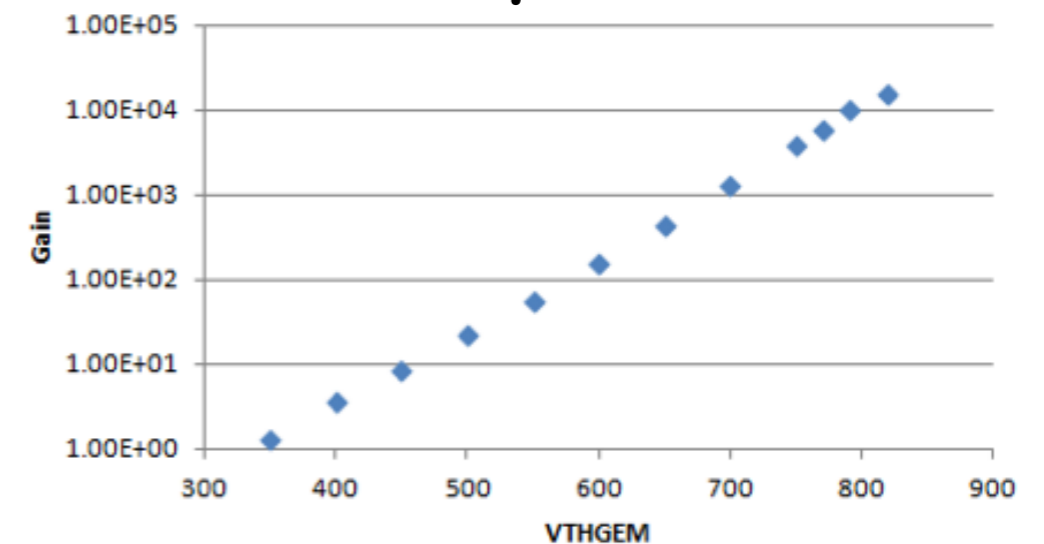
May 2012 batch - 30×30 mm² electrodes

- Geometry:
 - $a = 1\text{ mm}$, $d = 0.5\text{ mm}$, $t = 0.4\text{ mm}$,
 $h = 50 / 20 / 10\ \mu\text{m}$
- Dark currents:
 - $h = 50\ \mu\text{m} \rightarrow 0.004\text{ nA @ } 1\text{ kV}$
 $0.1\text{ nA @ } 1.5\text{ kV}$
 - $h = 20\ \mu\text{m} \rightarrow 0.2\text{-}0.4\text{ nA @ } 1\text{ kV}$
 - $h = 10\ \mu\text{m} \rightarrow 0.1\text{-}1\text{ nA @ } 1\text{ kV}$
- Maximal achievable gain
@ NeCH₄(5%):
 - $h = 50\ \mu\text{m} \rightarrow 2 \times 10^4$
 - $h = 20\ \mu\text{m} \rightarrow 2 \times 10^4$
 - $h = 10\ \mu\text{m} \rightarrow 8 \times 10^3$

20 μm rims

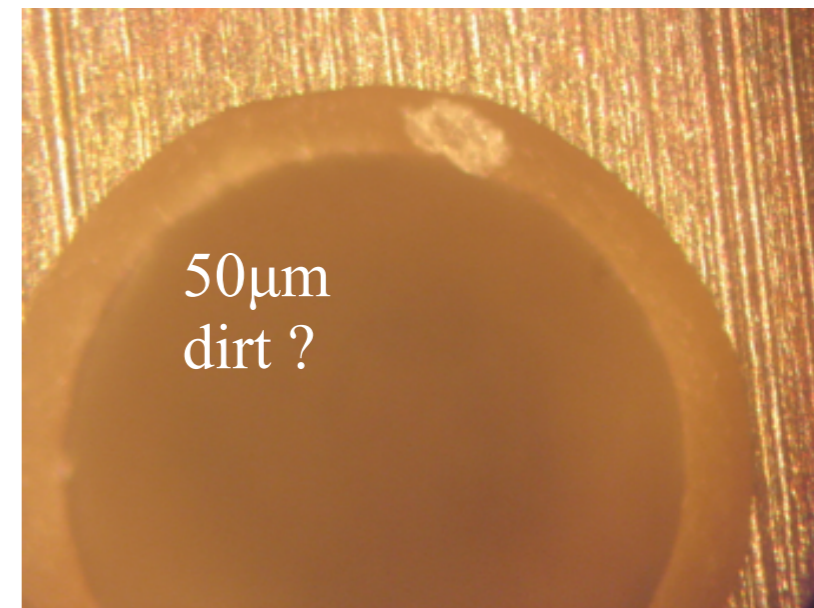
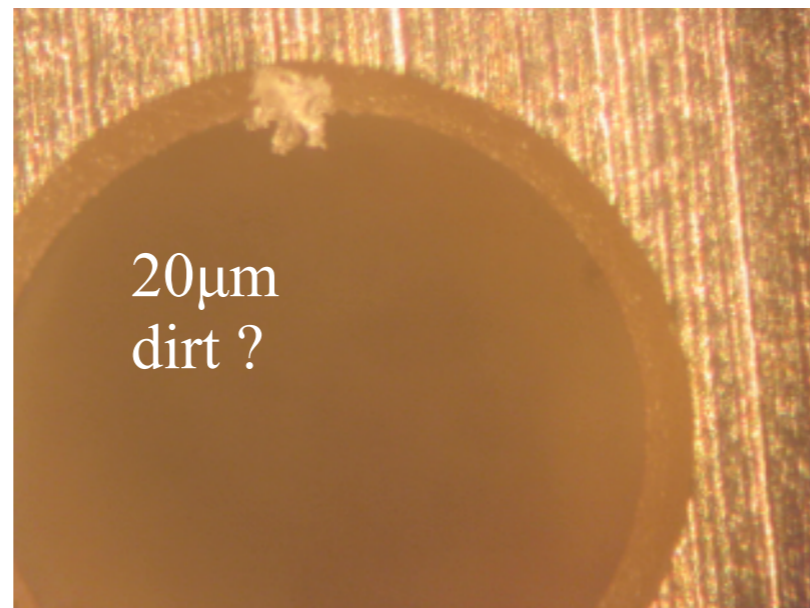
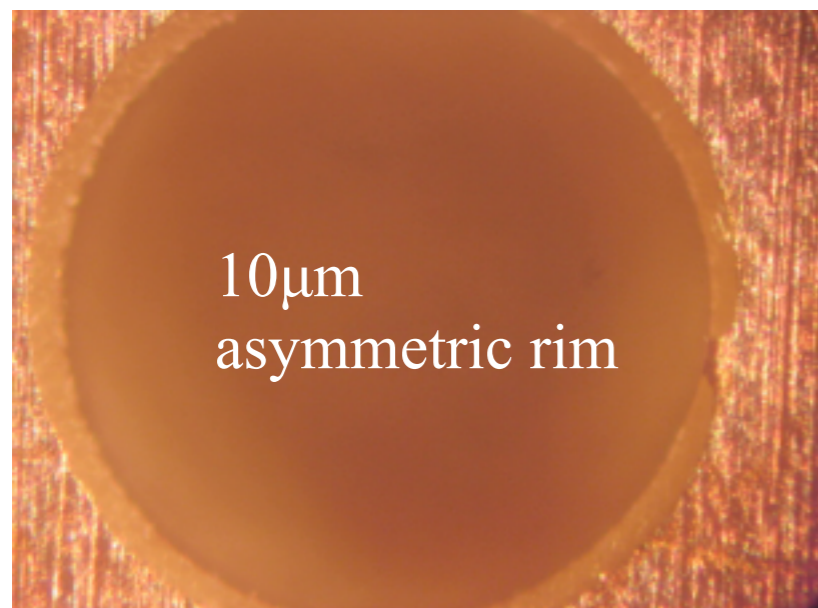


50 μm rims



- Conclusions: lower dark current, higher gains (and less sparks) are observed compared to the previous batch

May 2012 batch - snapshots of defects



- Not all the holes are perfect but the defect frequency is much lower
- There is still room for improving the de-smearing
- Any additional recommendations are welcomed
- The 30x30 mm² detectors appear stable we continued to a 100×100 mm² production, instructing PE to pay more attention to the de-smearing stage and final washing

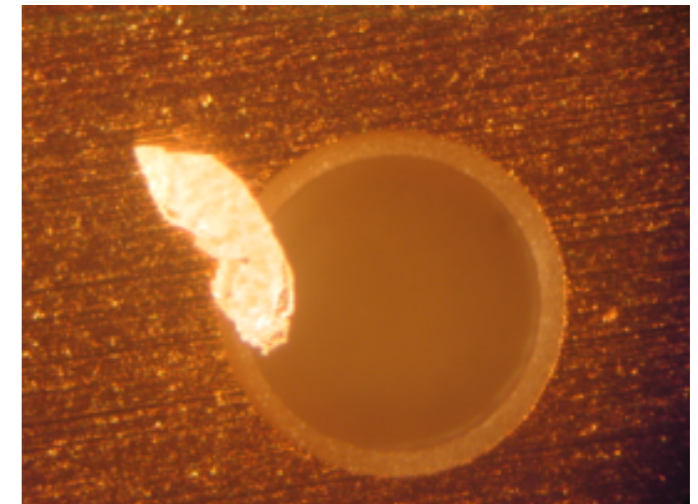
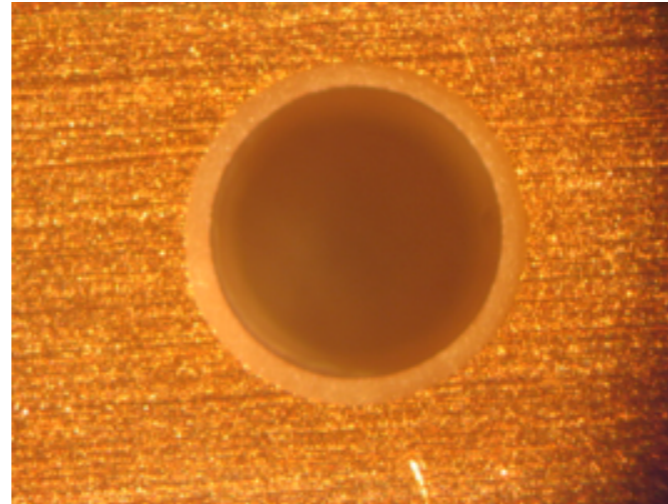
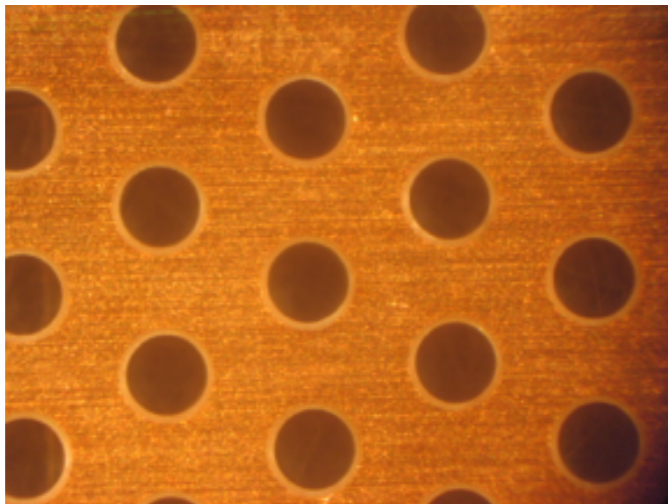
June 2012: 100×100 mm² electrodes

- Geometry:
 - $a = 1\text{ mm}$, $d = 0.5\text{ mm}$, $t = 0.4\text{ mm}$,
 $h = 100 / 50 / 20 / 10\ \mu\text{m}$

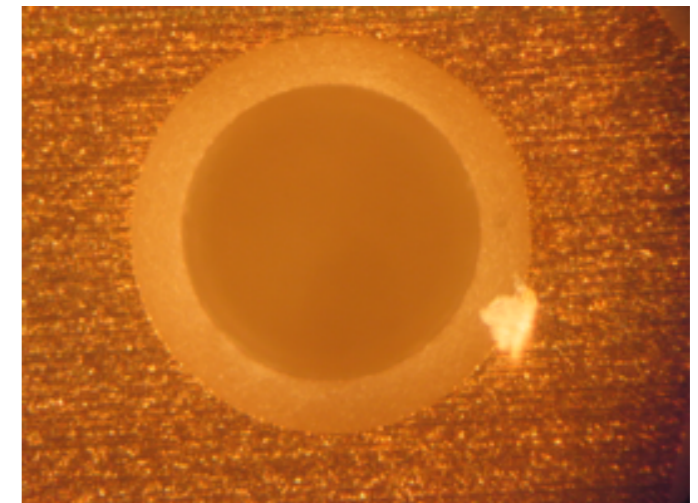
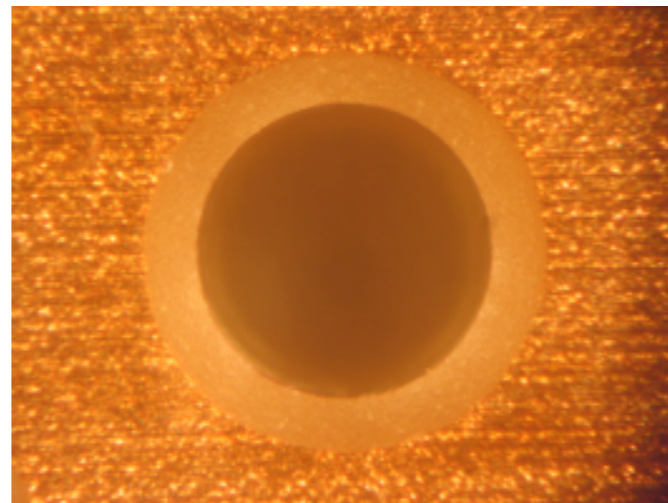
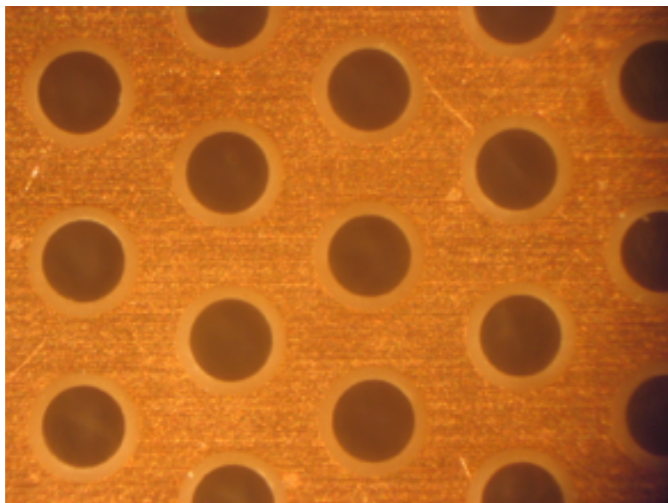
good hole

problematic hole ?

20 μm

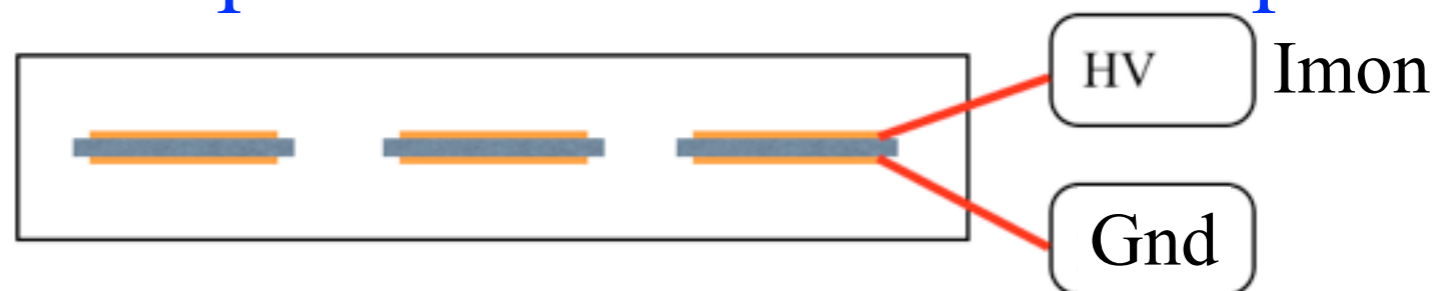


100 μm



Comparison to CERN production

- After additional baking
PE electrodes are compatible with the electrodes produced at CERN



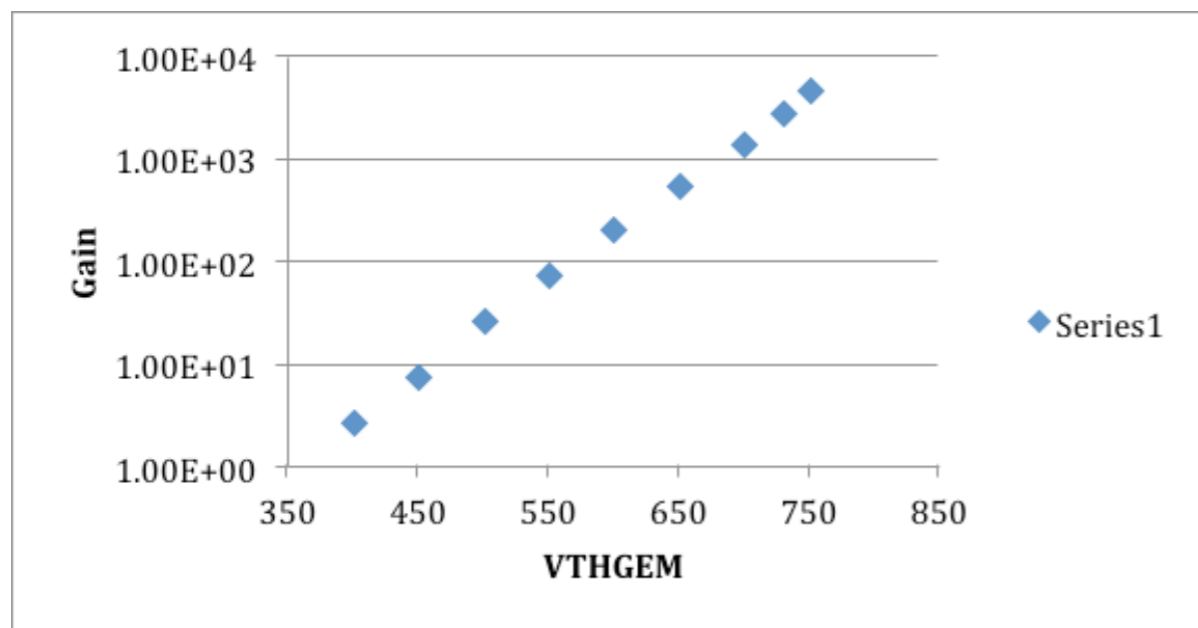
	CERN* 100 μm	PE 100 μm	PE 50 μm	PE 20 μm	PE 10 μm
I @ 1 kV	1 nA	< 1 nA	1 nA	< 1 nA	1 nA
I @ 1.5 kV	2 nA	< 1 nA	1 nA	1 nA	2 nA
I @ 2 kV	5 nA	2 nA	2 nA	2 nA	-
Sparks	2.3 kV	2.3 kV	2.4 kV	2.3 kV	2 kV

* Can be cleaned and probably improved

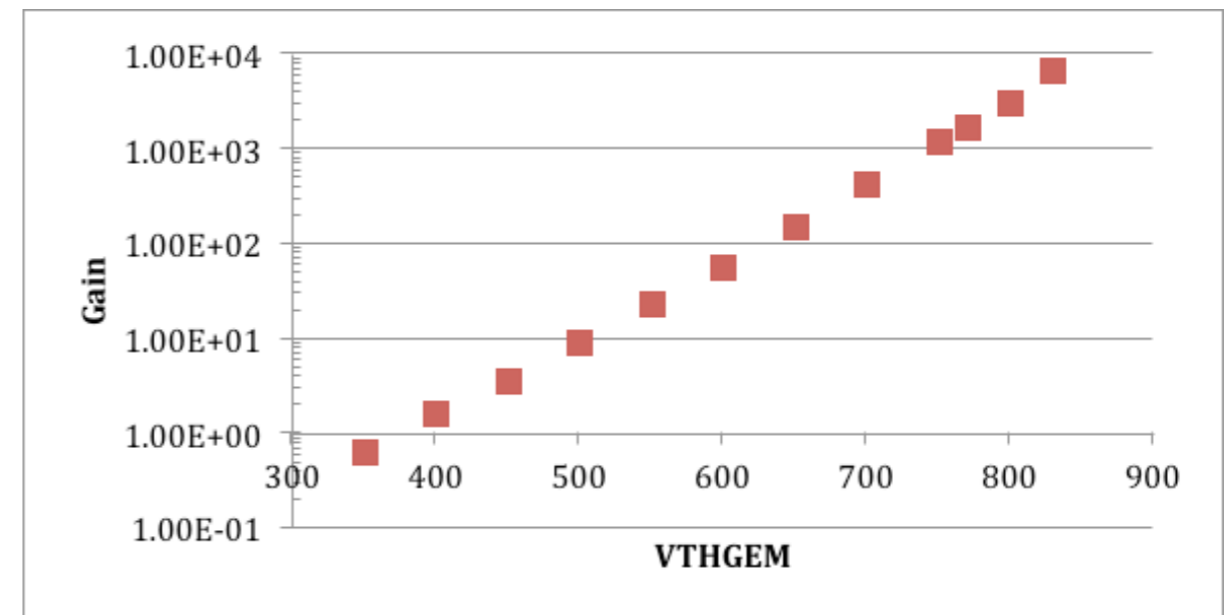
Comparison to CERN production

- Gain curves
- Measurements were taken before re-baking
 - An improvement is expected

20 μ m

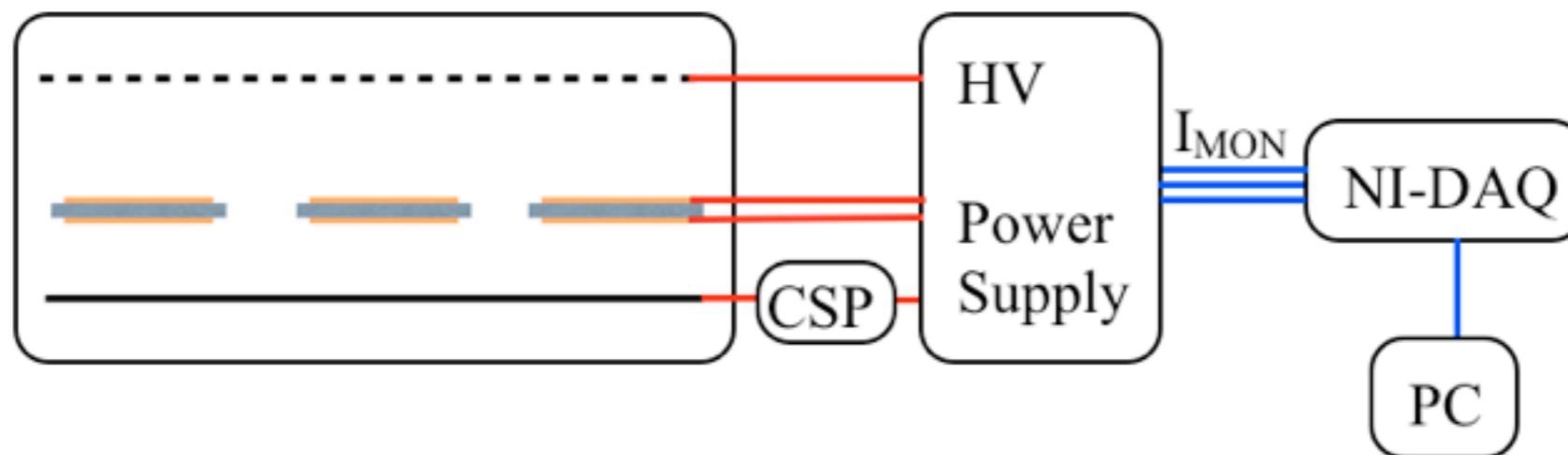


100 μ m



Prolonged spark rate measurement

- Two sources of discharge exist
 - Spontaneous (no radiation) due to defects
 - Radiation related
- In our QA evaluation we consider spontaneous discharges
- Setup scheme:



- We identified that some of the spark does not relate to the THGEM
- This effect is being studied

Future plan: 300×300 mm² electrodes

- Larger DHCAL prototype fully equipped with SRS electronics
- In collaboration with Aveiro and Coimbra
- Geometry:
 - $a = 1\text{ mm}$, $d = 0.5\text{ mm}$, $t = 0.4\text{ mm}$, $h = \#\#\ \mu\text{m}$?
- Segmentation:
 - Reducing detector segments capacitance
 - Any recommendations are welcomed
 - Strip width? number of segments? etc...
- Production date: as soon as the design is ready